



ERI C€

Feature

- · Width only 17.5mm (1SU)
- · 4:1 ultra wide input range
- -40~+85°C wide working temperature
- No minimum load required
- DC output adjustable ($\pm 10\%$)
- · Cooling by free air convection
- · Can be installed on DIN rail TS-35/7.5 or 15
- Protections: Short circuit / Overload / Over voltage / Input reverse polarity / Input under voltage protection
- 4KVdc I/O isolation(Reinforced isolation)
- 3 years warranty

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Applications

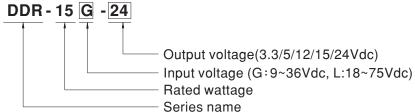
- · Industrial control system
- · Semi-conductor fabrication equipment
- Factory automation
- · Electro-mechanical
- · Wireless network
- · Telecom or datacom system

Description

DDR-15 series is a 15W DIN Rail type DC-DC converter with main features including DIN rail-type easy installation, ultra slim width (17.5mm), 4: 1 ultra wide input voltage, $-40 \sim +85^{\circ}$ C wide operating temperature, 4KVdc I/O isolation, adjustable output voltage (\pm 10%) and full protective functions...etc.

This series has two input options: $9\sim36\text{V}/18\sim75\text{V}$ and various output options: 3.3V/5V/12V/15V/24V and can be used for industrial control, security control, communication system and other fields. Suitable applications are DC buck/boost regulator, increasing system insulation level and voltage drop compensation along cable...etc.

■ Model Encoding





SPECIFICATION

Y (Typ.) IT (Typ.) RRENT (Typ.) AGE OLARITY TAGE LOCKOUT TEMP. IUMIDITY TEMP., HUMIDITY	3.0 ~ 3.6V ±2.0% ±0.5% ±1.5% 120ms, 85ms at full I G-type: 8ms@24Vdc 3300 µ F 9 ~ 36Vdc 84% 0.8A /24Vdc 110 ~ 150% rated ou Protection type : H 3.8 ~ 4.7V Protection type : Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	3300 μ F 84% stput power Hiccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p T, no damage, recovers a		17.25 ~ 20.25V	24V 0.63A 0 ~ 0.63A 15W 100mVp-p 21.6 ~ 28V ±2.0% ±0.5% ±0.5% 86% 28.8 ~ 32.4V					
RANGE VER DISE (max.) Note.2 DJ. RANGE DLERANCE Note.3 LATION JLATION E TIME ME (Typ.) CAPACITANCE) ANGE Note.4 ((Typ.) IT (Typ.) RRENT (Typ.) AGE OLARITY TAGE LOCKOUT EMP.	0 ~ 3.5A 11.6W 2 50mVp-p 3.0 ~ 3.6V ±2.0% ±0.5% ±1.5% 120ms, 85ms at full I G-type: 8ms@24Vdc 3300 μ F 9 ~ 36Vdc 84% 0.8A /24Vdc 15A /24Vdc 110 ~ 150% rated ou Protection type: H 3.8 ~ 4.7V Protection type: Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	0 ~ 3A 15W 50mVp-p 4.5 ~ 5.5V ±2.0% ±0.5% ±1% load cinput 3300 \(\mu \) F 84% stput power diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p 7, no damage, recovers a F < 8.5V	0 ~ 1.25A 15W 60mVp-p 9 ~ 13.2V ±2.0% ±0.5% ±0.5% 1200 μ F 85% 8 automatically after fault 13.8 ~ 16.2V over on to recover	0 ~ 1A 15W 75mVp-p 13.5 ~ 16.5V ±2.0% ±0.5% ±0.5% 1200 μ F 85% condition is removed 17.25 ~ 20.25V	0 ~ 0.63A 15W 100mVp-p 21.6 ~ 28V ±2.0% ±0.5% ±0.5% 680 μ F					
VER DISE (max.) Note.2 DJ. RANGE DLERANCE Note.3 LATION JLATION E TIME ME (Typ.) CAPACITANCE) ANGE Note.4 ('(Typ.) IT (Typ.) RRENT (Typ.) AGE OLARITY TAGE LOCKOUT EMP.	11.6W 2 50mVp-p 3.0 ~ 3.6V ±2.0% ±0.5% ±1.5% 120ms, 85ms at full I G-type: 8ms@24Vdc 3300 µ F 9 ~ 36Vdc 84% 0.8A /24Vdc 15A /24Vdc 110 ~ 150% rated ou Protection type: H 3.8 ~ 4.7V Protection type: Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	15W 50mVp-p 4.5 ~ 5.5V ±2.0% ±0.5% ±1% load c input 3300 μ F 84% stput power diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p Γ, no damage, recovers a	15W 60mVp-p 9 ~ 13.2V ±2.0% ±0.5% ±0.5% 1200 \(\mu\) F 85%	15W 75mVp-p 13.5 ~ 16.5V ±2.0% ±0.5% ±0.5% 1200 μ F 85% condition is removed 17.25 ~ 20.25V	15W 100mVp-p 21.6 ~ 28V ±2.0% ±0.5% ±0.5%					
DISE (max.) Note.2 DJ. RANGE DLERANCE Note.3 LATION JLATION E TIME ME (Typ.) CAPACITANCE) ANGE Note.4 ((Typ.) IT (Typ.) RRENT (Typ.) AGE OLARITY TAGE LOCKOUT EMP.	2 50mVp-p 3.0 ~ 3.6V ±2.0% ±0.5% ±1.5% 120ms, 85ms at full I G-type: 8ms@24Vdc 3300 µ F 9 ~ 36Vdc 84% 0.8A /24Vdc 15A /24Vdc 110 ~ 150% rated ou Protection type : H 3.8 ~ 4.7V Protection type : Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	50mVp-p 4.5 ~ 5.5V ±2.0% ±0.5% ±1% load cinput 3300 μ F 84% styput power diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p f, no damage, recovers a	60mVp-p 9 ~ 13.2V ±2.0% ±0.5% ±0.5% 1200 μ F 85%	75mVp-p 13.5 ~ 16.5V ±2.0% ±0.5% ±0.5% 1200 μ F 85% condition is removed 17.25 ~ 20.25V	100mVp-p 21.6 ~ 28V ±2.0% ±0.5% ±0.5%					
DJ. RANGE DLERANCE Note.3 LATION JLATION E TIME ME (Typ.) CAPACITANCE) ANGE Note.4 ('(Typ.) IT (Typ.) RRENT (Typ.) AGE OLARITY TAGE LOCKOUT EMP. IUMIDITY	3.0 ~ 3.6V ±2.0% ±0.5% ±1.5% 120ms, 85ms at full I G-type: 8ms@24Vdc 3300 µ F 9 ~ 36Vdc 84% 0.8A /24Vdc 110 ~ 150% rated ou Protection type : H 3.8 ~ 4.7V Protection type : Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	4.5 ~ 5.5V ±2.0% ±0.5% ±10.5% ±11% load cinput 3300 μ F 84% stput power diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p Γ, no damage, recovers a F ≤ 8.5V	9 ~ 13.2V ±2.0% ±0.5% ±0.5% 1200 μ F 85%	13.5 ~ 16.5V ±2.0% ±0.5% ±0.5% 1200 μ F 85% condition is removed 17.25 ~ 20.25V	21.6 ~ 28V ±2.0% ±0.5% ±0.5%					
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E TIME ME (Typ.) CAPACITANCE) ANGE Note.4 ((Typ.) IT (Typ.) RRENT (Typ.) AGE OLARITY TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	120ms, 85ms at full I G-type: 8ms@24Vdc 3300 µ F 9 ~ 36Vdc 84% 0.8A /24Vdc 15A /24Vdc 110 ~ 150% rated ou Protection type : H 3.8 ~ 4.7V Protection type : Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	±1% load 3300 μ F 84% stput power diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p Γ, no damage, recovers a	1200 μ F 85% s automatically after fault 13.8 ~ 16.2V ower on to recover	±0.5% 1200 μ F 85% condition is removed 17.25 ~ 20.25V	±0.5% 680 μ F 86%					
E TIME ME (Typ.) CAPACITANCE) ANGE Note.4 ((Typ.) IT (Typ.) RRENT (Typ.) AGE OLARITY TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	G-type: 8ms@24Vdc 3300 µ F 9 ~ 36Vdc 84% 0.8A /24Vdc 15A /24Vdc 110 ~ 150% rated ou Protection type : H 3.8 ~ 4.7V Protection type : Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	3300 μ F 84% stput power Hiccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p T, no damage, recovers a	85% s automatically after fault 13.8 ~ 16.2V ower on to recover	1200 μ F 85% condition is removed 17.25 ~ 20.25V	86%					
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CAPACITANCE) ANGE Note.4 ((Typ.) IT (Typ.) RRENT (Typ.) AGE OLARITY TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	3300 µ F 9 ~ 36Vdc 84% 0.8A /24Vdc 15A /24Vdc 110 ~ 150% rated ou Protection type : H 3.8 ~ 4.7V Protection type : Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	3300 µ F 84% stput power diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p r, no damage, recovers a r∈ ≪8.5V	85% s automatically after fault 13.8 ~ 16.2V ower on to recover	condition is removed	86%					
Y (Typ.) IT (Typ.) RRENT (Typ.) AGE OLARITY TAGE LOCKOUT TEMP. IUMIDITY TEMP., HUMIDITY	84% 0.8A /24Vdc 15A /24Vdc 110 ~ 150% rated out Protection type: H 3.8 ~ 4.7V Protection type: Shut By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer to	utput power Hiccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p T, no damage, recovers a	s automatically after fault 13.8 ~ 16.2V ower on to recover	condition is removed 17.25 ~ 20.25V						
AGE OLARITY TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	0.8A /24Vdc 15A /24Vdc 110 ~ 150% rated ou Protection type: H 3.8 ~ 4.7V Protection type: Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	utput power Hiccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p T, no damage, recovers a	s automatically after fault 13.8 ~ 16.2V ower on to recover	condition is removed 17.25 ~ 20.25V						
RRENT (Typ.) AGE OLARITY TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	15A /24Vdc 110 ~ 150% rated ou Protection type : H 3.8 ~ 4.7V Protection type : Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p F, no damage, recovers a	13.8 ~ 16.2V ower on to recover	17.25 ~ 20.25V	28.8 ~ 32.4V					
AGE OLARITY TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	110 ~ 150% rated ou Protection type: H 3.8 ~ 4.7V Protection type: Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p F, no damage, recovers a	13.8 ~ 16.2V ower on to recover	17.25 ~ 20.25V	28.8 ~ 32.4V					
AGE OLARITY TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	Protection type: H 3.8 ~ 4.7V Protection type: Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p F, no damage, recovers a	13.8 ~ 16.2V ower on to recover	17.25 ~ 20.25V	28.8 ~ 32.4V					
AGE OLARITY TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	Protection type: H 3.8 ~ 4.7V Protection type: Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	diccup mode, recovers 5.75 ~ 7V ut down o/p voltage, re-p F, no damage, recovers a	13.8 ~ 16.2V ower on to recover	17.25 ~ 20.25V	28.8 ~ 32.4V					
OLARITY .TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	3.8 ~ 4.7V Protection type: Shu By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	5.75 ~ 7V ut down o/p voltage, re-p , no damage, recovers a F 8.5V	13.8 ~ 16.2V ower on to recover	17.25 ~ 20.25V	28.8 ~ 32.4V					
OLARITY .TAGE LOCKOUT EMP. IUMIDITY EMP., HUMIDITY	By internal MOSFET Power ON≥9V, OF -40 ~ +85°C (Refer t	Γ, no damage, recovers a F≤8.5V		tion removed						
TAGE LOCKOUT EMP. HUMIDITY EMP., HUMIDITY	Power ON≥9V, OF -40 ~ +85°C (Refer t	F≤8.5V	utomatically after fault condi	tion removed						
EMP. IUMIDITY EMP., HUMIDITY	Power ON≥9V, OF -40 ~ +85°C (Refer t	F≤8.5V			By internal MOSFET, no damage, recovers automatically after fault condition removed					
IUMIDITY EMP., HUMIDITY	-40 ~ +85°C (Refer t			Power ON>9V, OFF < 8.5V						
IUMIDITY EMP., HUMIDITY	,		-40 ~ +85°C (Refer to "Derating Curve")							
EMP., HUMIDITY		5 ~ 95% RH non-condensing								
	-40 ~ +85°C, 5 ~ 95% RH non-condensing									
FICIENT	±0.03%/°C (0~60°C)									
	Component: 10 ~ 500Hz, 2G 10min./1cycle, 60min. each along X, Y, Z axes; Mounting: Compliance to IEC60068-2-6									
G ALTITUDE	2000 meters									
ANDARDS	IEC 62368-1 (LVD) approved, Design refer to UL508									
VOLTAGE	I/P-O/P:4KVdc									
RESISTANCE	I/P-O/P>100M Ohms / 500Vdc / 25°C / 70% RH									
1120101711102	Parameter		Standard	Test Level / Note						
EMC EMISSION			EN55032	Class B						
	1									
EMC IMMUNITY										
				Level 3, 8KV air : Level 3, 6KV contact; criteria						
	-									
	-									
	9		_INU IUUU-4-0	Level 4, SUA/III , CITTERIA A						
	,									
	neters NOT specific are meass e: includes set may be neededer supply is conditionally directives. For example, and the second of the second contractives are supply is conditionally directives.	Voltage Flicker EN55024 , EN61000 Parameter ESD Radiated EFT / Burst Surge Conducted Magnetic Field 907K hrs min. MI 17.5*90*54.5mm (W 68g; 160pcs/12Kg/1 neters NOT specially mentioned are noise are measured at 20MHz of bite: includes set up tolerance, line re may be needed under low input volver supply is considered as an indep of directives. For guidance on how to able on http://www.meanwell.com)	Voltage Flicker EN55024 , EN61000-6-2(EN50082-2) Parameter ESD Radiated EFT / Burst Surge Conducted Magnetic Field 907K hrs min. MIL-HDBK-217F (25°C) 17.5*90*54.5mm (W*H*D) 68g; 160pcs/12Kg/1.19CUFT meters NOT specially mentioned are measured at 24VDC is noise are measured at 20MHz of bandwidth by using a 12 se : includes set up tolerance, line regulation and load regulat	Voltage Flicker EN55024 , EN61000-6-2(EN50082-2) Parameter ESD EN61000-4-2 Radiated EFT / Burst Surge EN61000-4-5 Conducted Magnetic Field 907K hrs min. MIL-HDBK-217F (25°C) 17.5*90*54.5mm (W*H*D) 68g; 160pcs/12Kg/1.19CUFT meters NOT specially mentioned are measured at 24VDC input, rated load and 25°C noise are measured at 20MHz of bandwidth by using a 12" twisted pair-wire termine: includes set up tolerance, line regulation and load regulation. may be needed under low input voltage. Please check the derating curve for more ver supply is considered as an independent unit, but the final equipment still need to a directives. For guidance on how to perform these EMC tests, please refer to "EMI able on http://www.meanwell.com)	Voltage Flicker EN55024 , EN61000-6-2(EN50082-2) Parameter Standard EN61000-4-2 ESD EN61000-4-3 Evel 3, 8KV air ; Lev Radiated EN61000-4-3 Evel 3, 10V/m ; criteria Surge EN61000-4-5 Conducted EN61000-4-6 EN61000-4-6 Level 3, 1VV/Line-Lin Conducted EN61000-4-8 Level 3, 10V ; criteria Magnetic Field EN61000-4-8 Level 4, 30A/m ; criteria 907K hrs min. MIL-HDBK-217F (25°C) 17.5*90*54.5mm (W*H*D) 68g; 160pcs/12Kg/1.19CUFT Interest NOT specially mentioned are measured at 24VDC input, rated load and 25°C of ambient temperature noise are measured at 20MHz of bandwidth by using a 12" twisted pair-wire terminated with a 0.1 \(\mu \) f & 47 to e: includes set up tolerance, line regulation and load regulation. may be needed under low input voltage. Please check the derating curve for more details. The supply is considered as an independent unit, but the final equipment still need to re-confirm that the who is directives. For guidance on how to perform these EMC tests, please refer to "EMI testing of component possible on http://www.meanwell.com) Directives models and of 5°C/1000m with fan models for operation.					



SPECIFICATION

MODEL		DDR-15L-3.3	DDR-15L-5	DDR-15L-12	DDR-15L-15	DDR-15L-24		
	DC VOLTAGE	3.3V	5V	12V	15V	24V		
	RATED CURRENT	4.5A	3A	1.25A	1A	0.63A		
	CURRENT RANGE	0 ~ 4.5A	0 ~ 3A	0 ~ 1.25A	0 ~ 1A	0 ~ 0.63A		
	RATED POWER	15W	15W	15W	15W	15W		
	RIPPLE & NOISE (max.) Note.2		50mVp-p	60mVp-p	75mVp-p	100mVp-p		
	VOLTAGE ADJ. RANGE	3.0 ~ 3.6V	4.5 ~ 5.5V	9 ~ 13.2V	13.5 ~ 16.5V	26.1 ~ 28V		
OUTPUT	VOLTAGE TOLERANCE Note.3		±2.0%	±2.0%	±2.0%	±2.0%		
	LINE REGULATION	±0.5%	±0.5%	±0.5%	±0.5%	±0.5%		
	LOAD REGULATION	±1.5%	±1%	±0.5%	±0.5%	±0.5%		
	SETUP. RISE TIME	120ms, 85ms at full lo	±0.570					
	HOLD UP TIME (Typ.)	L-type: 16ms@48Vdc input						
	EXTERNAL CAPACITANCE	71						
	LOAD (Max.)	3300 μ F	3300 μ F	1200 μ F	1200 μ F	680 μ F		
	VOLTAGE RANGE Note.4	18 ~ 75Vdc		<u> </u>	<u> </u>			
	EFFICIENCY (Typ.)	84%	85%	86%	86%	87%		
INPUT	DC CURRENT (Typ.)	0.4A /48Vdc	,		•			
	INRUSH CURRENT (Typ.)	15A/48Vdc						
	(31)	110 ~ 150% rated out	put power					
	OVERLOAD			ers automatically after fault	condition is removed			
PROTECTION		3.8 ~ 4.7V	5.75 ~ 7V	13.8 ~ 16.2V	17.25 ~ 20.25V	28.8 ~ 32.4V		
KOTECTION	OVER VOLTAGE	*** ****			11.20 20.201	25.0 02.71		
	REVERSE POLARITY	Protection type: Shut down o/p voltage, re-power on to recover By internal MOSFET, no damage, recovers automatically after fault condition removed						
	UNDER VOLTAGE LOCKOUT	By Internal MOSFE I, no damage, recovers automatically after fault condition removed Power ON≥18V , OFF≤17V						
	WORKING TEMP.	-40 ~ +85°C (Refer to "Derating Curve")						
		5 ~ 95% RH non-condensing						
-NVIDONMENT	WORKING HUMIDITY	-40 ~ +85°C, 5 ~ 95% RH non-condensing						
ENVIRONMENT	STORAGE TEMP., HUMIDITY	±0.03%°C (0~60°C)						
	TEMP. COEFFICIENT	,		00 : 1 1 2 2 2 7	M (' 0 1' 1	1500000000		
	VIBRATION OPERATING ALTITUDE	· ·	Hz, 2G 10min./1cycle	, 60min. each along X, Y, Z axe	es; Mounting: Compliance to	0 IEC60068-2-6		
	OPERATING ALTITUDE	2000 meters IEC 62368-1 (LVD) approved, Design refer to UL508						
	SAFETY STANDARDS	I/P-O/P:4KVdc						
	WITHSTAND VOLTAGE							
	ISOLATION RESISTANCE	I/P-O/P>100M Ohms / 500Vdc / 25°C / 70% RH						
		Parameter		Standard	Test Level / Note			
		Conducted		EN55032	Class B			
	EMC EMISSION	Radiated		EN55032	Class B			
SAFETY &		Voltage Flicker		EN61000-3-3				
EMC		EN55024 , EN61000-	6-2(EN50082-2)					
(Note 5)	EMC IMMUNITY	Parameter		Standard	Test Level / Note			
		ESD		EN61000-4-2	Level 3, 8KV air ; Level 3, 6KV contact; criter			
		Radiated		EN61000-4-3	Level 3, 10V/m ; criteria A			
		EFT / Burst		EN61000-4-4	Level 3, 2KV ; criteria A			
		Surge		EN61000-4-5	Level 3, 1KV/Line-Line ; criteria A			
		Conducted		EN61000-4-6	Level 3, 10V; criteria A			
		Magnetic Field		EN61000-4-8	Level 4, 30A/m; criteria A			
	MTBF	907K hrs min. MIL						
OTHERS	DIMENSION	17.5*90*54.5mm (W*H*D)						
	PACKING	68g; 160pcs/12Kg/1.19CUFT						
NOTE	Ripple & noise are measured: Tolerance: includes set under the control of the control o	cially mentioned are measured at 48VDC input, rated load and 25 $^{\circ}$ C of ambient temperature. ured at 20MHz of bandwidth by using a 12" twisted pair-wire terminated with a 0.1 μ f & 47 μ f parallel capacitor. up tolerance, line regulation and load regulation. under low input voltage. Please check the derating curve for more details. sidered as an independent unit, but the final equipment still need to re-confirm that the whole system complies with guidance on how to perform these EMC tests, please refer to "EMI testing of component power supplies."						

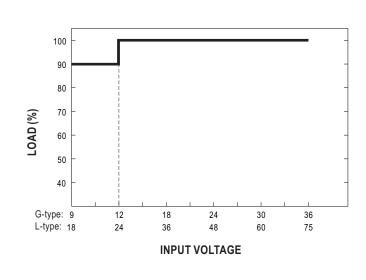


■ Block Diagram fosc: 100KHz **RECTIFIERS** POWER EMI I/P O-& FILTER **FILTER** SWITCHING -O -Vo DETECTION PWM CONTROL CIRCUIT O.L.P. 0.V.P. ■ Derating Curve 100 LOAD (%)

75 85 (VERTICAL)

■ Output derating VS input voltage

-40 -30 -20 -10 0



10 20

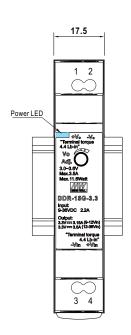
AMBIENT TEMPERATURE (°C)

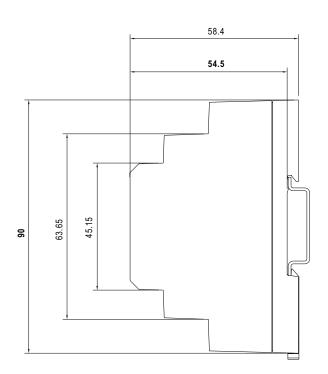
30

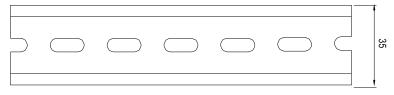


■ Mechanical Specification

(Unit: mm, tolerance ± 0.5mm)







ADMISSIBLE DIN-RAIL:TS35/7.5 OR TS35/15

Terminal Pin No. Assignment

Pin No.	Assignment			
1	DC Output +Vo			
2	DC Output -Vo			
3	DC Input -Vin			
4	DC Input +Vin			

■ Installation Manual

Please refer to : http://www.meanwell.com/manual.html